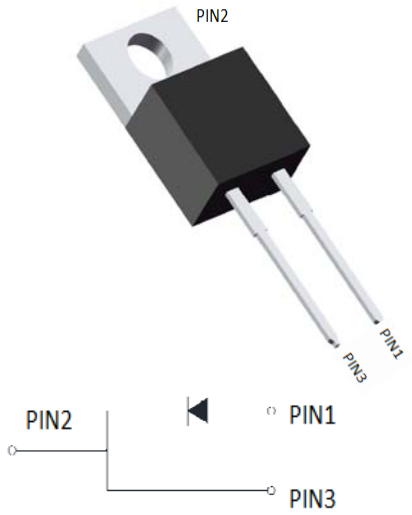
Schottky Diodes



Features

- High frequency operation
- Low forward voltage drop
- High purity, high temperature epoxy encapsulation for enhanced mechanical strength and moisture resistance
- Guard ring for enhanced ruggedness and long term reliability
- Solder dip 275 °C max. 7 s, per JESD 22-B106

Typical Applications

Typical applications are in switching power supplies, converters, freewheeling diodes, and reverse battery protection.

Mechanical Data

- **Package**: TO-220AC
  Molding compound meets UL 94 V-0 flammability rating, RoHS-compliant
- **Terminals**: Tin plated leads, solderable per J-STD-002 and JESD22-B102
- **Polarity**: As marked

■Maximum Ratings (Ta=25℃ Unless otherwise specified)

PARAMETER	SYMBOL	UNIT	MBR10100	MBR10150	MBR10200
Device marking code			MBR10100	MBR10150	MBR10200
Repetitive Peak Reverse Voltage	V_{RRM}	V	100	150	200
Average Rectified Output Current @60Hz sine wave, R-load, Ta=25℃	I_O	A	10		
Surge(Non-repetitive)Forward Current @60Hz half sine-wave, 1 cycle, Ta=25℃	I_{FSM}	A	150		
Current Squared Time @1ms≤t≤8.3ms Tj=25℃,	I^2t	A^2s	94		
Storage Temperature	T_{stg}	℃	-55 ~ +175		
Junction Temperature	T_j	℃	-55 ~ +175		

■Electrical Characteristics (Ta=25℃ Unless otherwise specified)

PARAMETER	SYMBOL	UNIT	TEST CONDITIONS	MBR10100	MBR10150	MBR10200
Maximum instantaneous forward voltage drop per diode	V_{FM}	V	I_{FM}=10.0A	0.8	0.85	0.9
Maximum DC reverse current at rated DC blocking voltage per diode	I_{RRM1}	uA	$V_{RM}=V_{RRM}$ Ta=25℃	50		
	I_{RRM2}	mA	$V_{RM}=V_{RRM}$ Ta=100℃	5		

Note1:Pulse test:300uS pulse widh,1% duty cycle

Note2:Pulse test:pulse widh 40mS

■Thermal Characteristics （T_a=25℃ Unless otherwise specified）

PARAMETER		SYMBOL	UNIT	MBR10100	MBR10150	MBR10200
Thermal Resistance	Between junction and case	$R\theta_{J-C}$	℃/W	2.0		

■Ordering Information (Example)

PREFERED P/N	UNIT WEIGHT(g)	MINIIMUM PACKAGE(pcs)	INNER BOX QUANTITY(pcs)	OUTER CARTON QUANTITY(pcs)	DELIVERY MODE
MBR10100 THRU MBR10200	Approximate 1.8	50	1000	5000	Tube

■Characteristics (Typical)

FIG1:Io -Tc Curve

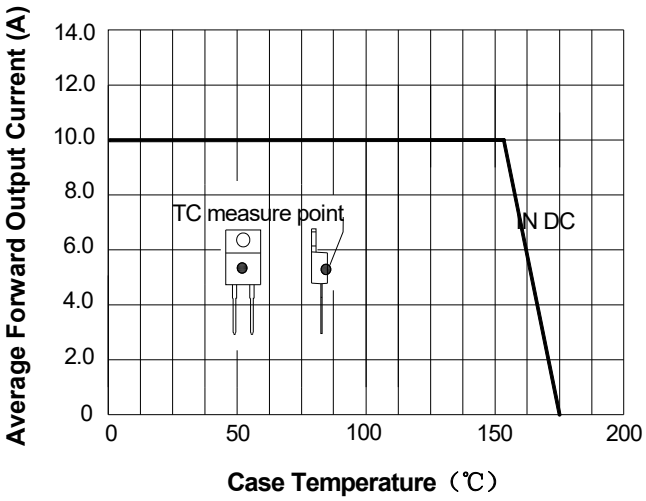


FIG2:Surge Forward Current Capability

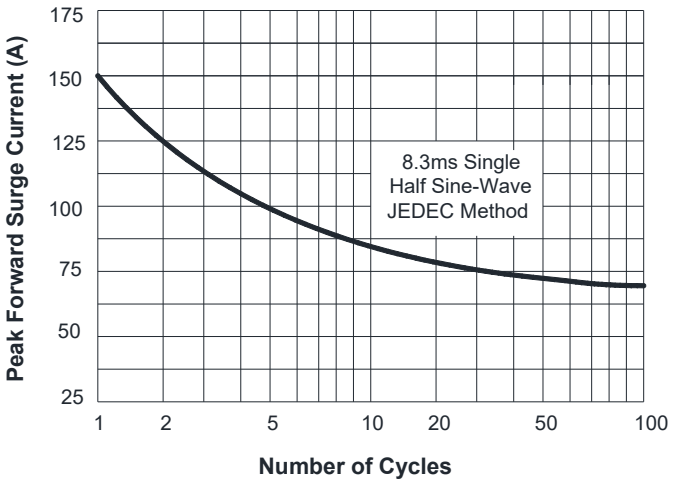


FIG3: Forward Voltage

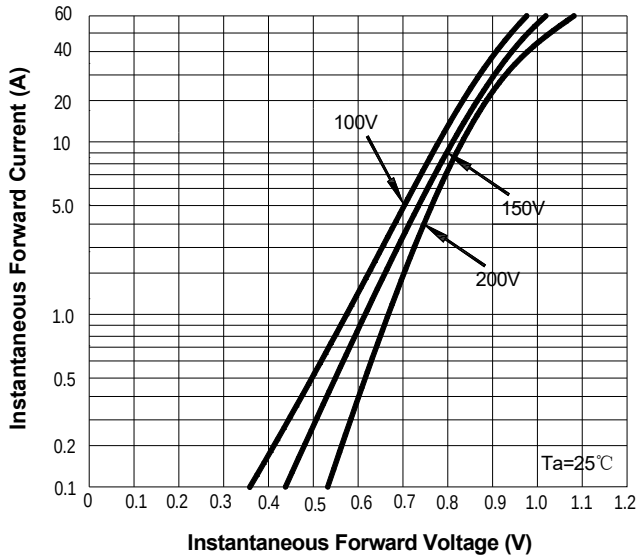
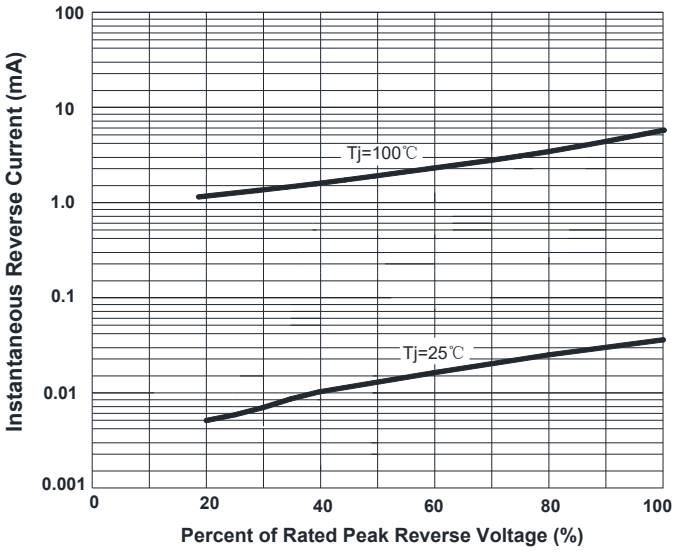
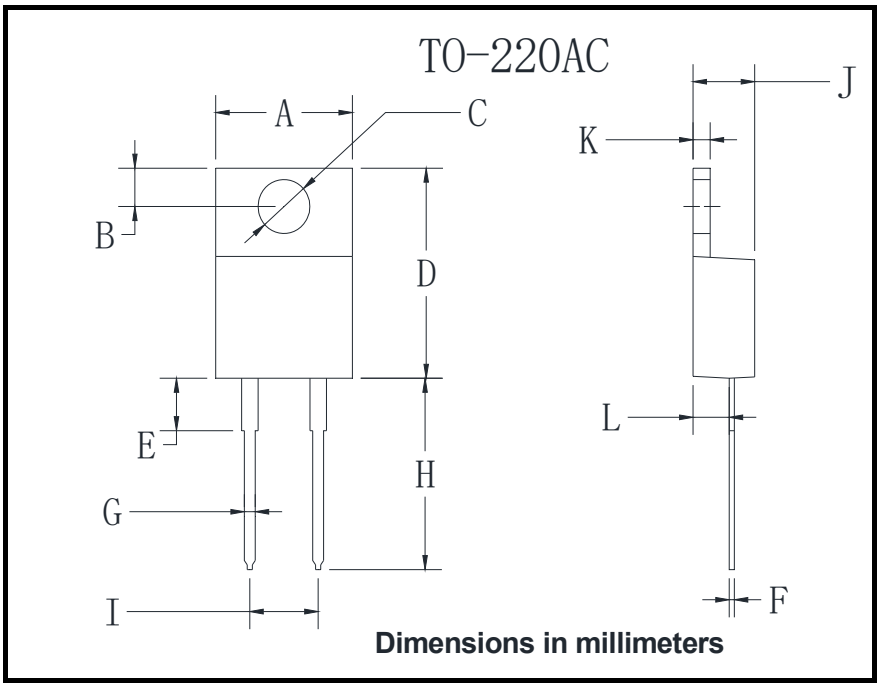


FIG.4: Typical Rrverse Characteristics



■Outline Dimensions



TO-220AC		
Dim	Min	Max
A	9.95	10.35
B	2.55	2.95
C	3.75	4.05
D	14.95	15.25
E	3.75	4.25
F	0.26	0.5
G	0.68	0.94
H	13.3	13.9
I	4.86	5.26
J	4.38	4.78
K	1.14	1.4
L	2.37	2.79

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